Pressure-induced high temperature superconductivity in $\text{H}_3\text{X}$ ($\text{X}=\text{As, Se, Br, Sb, Te and I}$)

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The discovery of high critical temperature $T_c$ superconductivity in highly compressed $\text{H}_3\text{S}$ has opened up the question of searching for strong electron-phonon coupling in the hydrides outside the transition metal series. The specific objective of this work is to explore the possibility of discovering a material that exceeds the superconducting transition temperature of $\text{H}_3\text{S}$. Our study includes the materials $\text{H}_3\text{X}$ ($\text{X}=\text{As, Se, Br, Sb, Te, and I}$), is limited to the $\text{Im}\overline{3}m$ crystal structure. The procedure we adopt involves performing linearized augmented plane wave (LAPW) calculations for many different volumes to compute the electronic densities of states and their pressure variation. This is combined with Quantum-ESPRESSO (QE) calculations from which we obtain the phonon frequencies and the electron-phonon coupling constant $\lambda$, and followed by applying the multiple scattering-based theory of Gaspari and Gyorffy (GG) to obtain the Hopfield parameters and the McMillan-Allen-Dynes theory. It should be stressed that the GG approach decouples the electronic contribution to $\lambda$ from the corresponding phonon contribution, and provides additional insights for the understanding of superconductivity in these materials. Based on our analysis, the hydrogen is the main contributor to the $T_c$ in these materials as it makes up 75 $\sim$ 80% of the total $\lambda$. Our calculations for $\text{H}_3\text{Se}$ and $\text{H}_3\text{Br}$ give a $T_c \sim 100$ K. For the other materials in our study we find that $\text{H}_3\text{As}$ is unstable and $\text{H}_3\text{Sb}$, $\text{H}_3\text{Te}$ and $\text{H}_3\text{I}$ have small values of the McMillan-Hopfield parameters which makes it unlikely to give high $T_c$. However, according to both of our rigid band model and virtual crystal calculations, we predict a $T_c \sim 150$ K for $\text{H}_3\text{Br}$ with a small amount of hydrogen doping. Our basic conclusion is that the materials studied here could not reach very high $T_c$ because the Hopfield parameters, which are the strongest contributor to high $T_c$, are not large enough.

PACS numbers:

I. INTRODUCTION

Recently high temperature superconductivity at temperatures exceeding 200 K was predicted by Duan et al. [1] at extreme pressures above 200 GPa in $\text{H}_3\text{S}$ in the $\text{Im}\overline{3}m$ crystal structure. [2] The prediction was immediately confirmed experimentally by Drozdov et al. [3]. This breakthrough has motivated numerous theoretical and experimental studies [4–19] and the consensus developed that conventional BCS electron-phonon coupling is in play. Researchers in this field are exploring other elements to stabilize hydrogen at high pressures and already have been reports of near room temperature (RT) superconductivity in the compound $\text{H}_3\text{La}$ [7, 15]. The idea of metallization of hydrogen that was proposed long ago by Wigner and Huntington [20] has been pursued vigorously and Ashcroft’s prediction [21] of RT superconductivity in metallic hydrogen under high pressures is getting close to reality.

Using the Gaspari–Gyorffy (GG) theory [22], which is the basis of the present work, Papaconstantopoulos and Klein [23] predicted the electron-phonon coupling $\lambda = 1.86$ and superconducting temperature $T_c = 234$ K at a pressure of 460 GPa for metallic hydrogen.

However, metallizing hydrogen requires extremely high pressure [20]. Recent theoretical studies also suggest that it would require pressure at roughly 500 GPa [24]. The hydrides are thus introduced as an alternative which offer a rather satisfactory trade-off since they could form metallic states at much lower pressure.

The hydrides are considered as unusual but conventional superconductors since their behavior can be explained with traditional electron-phonon interaction while a few details differ from the conventional ones [25]. A comprehensive review of superconductivity in hydrides is given by Zurek et al. [26]. $\text{H}_3\text{S}$ is a prominent example because of its optimal electronic states and the separation of the acoustic from the optical phonon modes. It is believed that sulfur lacks a specific role in terms of its contribution to enhancing superconductivity but it helps hydrogen forming metallic states. To carry this idea forward, there have been several attempts at targeting other hydrides, replacing sulfur with different elements within the same $\text{Im}\overline{3}m$ crystal structure [4, 8, 9, 12], which includes isoelectronic counterparts such as Se [5, 10, 12].

Although it is commonly accepted that hydrogen is the main contributor to $T_c$ in $\text{H}_3\text{S}$, other hydride-forming elements may have a dramatic impact on the hydrogen contribution. The purpose of this work is to present a comprehensive study of the electronic structure of the hydrides $\text{H}_3\text{X}$ ($\text{X}=\text{As, Se, Br, Sb, Te and I}$) in the $\text{Im}\overline{3}m$ crystal structure and using the GG theory to calculate the Hopfield parameter $\eta$. To explore the possible superconducting properties of these materials and compare...
with the well established H\textsubscript{3}S, we make estimates of the phonon frequencies from Refs. \cite{5,19} and we conclude that a large value of the \( \eta \) parameter is the strongest indication of high \( T_c \) in these materials as in the case in H\textsubscript{3}S.

II. COMPUTATIONAL DETAILS

The electronic structure calculations are performed with the all-electron Linearized Augmented Plane Wave (LAPW) method \cite{27} specifically the Wei-Krakauer-Singh code \cite{28} developed at the U.S. Naval Research Laboratory. In the present calculations the Hedin-Lundqvist form of the local density approximation was used.\cite{29}

To ensure sufficient accuracy for convergence, the total and orbital-projected densities of electronic states (pDOS) are calculated by the tetrahedron method with a uniformly distributed k-point grid of 1785 k-points in the irreducible Brillouin zone.

The key step to estimate \( T_c \) is the determination of the electron-phonon coupling \( \lambda \), which, as pointed out by McMillan \cite{30} and Hopfield \cite{31}, can be written as

\[
\lambda_j = \frac{\eta_j}{M_j}\frac{N(E_F)\langle I_j^2 \rangle}{M_j\langle \omega_j^2 \rangle} \tag{1}
\]

where \( N(E_F) \) is the total DOS per spin at the Fermi level \( E_F \), \( \langle I_j^2 \rangle \) is the electron–ion matrix element, \( \langle \omega_j^2 \rangle \) is the average phonon frequency and the index \( j \) corresponds to X element and hydrogen. The Hopfield parameter \( \eta_j \), which only describes electronic properties, is calculated using the GG formula based on the scattering theory. This formula allows us to express the electronic contributions to the \( \lambda_j \) in local terms in the following form

\[
\eta_j = \frac{1}{N(E_F)}\sum_{l=0}^{2}(l+1)\sin^2(\delta_l^j - \delta_{l+1}^j)u_l^j u_{l+1}^j \tag{2}
\]

where both \( \delta_l^j \) and \( v_l^j = N_l^j(\epsilon_F)/N_l^{j(1)} \) are orbital l and site j dependent. The phase shifts \( \delta_l^j \) are defined through the following equation:

\[
tan(\delta(R_s,E)) = \frac{j_l^j - j_l(kR_s)L_l(R_s,E)}{n_l^j - n_l(kR_s)L_l(R_s,E)}, \tag{3}
\]

where \( L_l = u_l^j/u_l \) is the logarithmic derivative and \( j_l \) and \( n_l \) are spherical Bessel and Neumann functions. The free scatterer DOS \( N_l^{j(1)} \) is defined as follows:

\[
N_l^{j(1)} = (2l+1)\int_0^{R_s} \left[u_l^j(r,E_F)\right]^2 r^2dr \tag{4}
\]

where \( u_l^j \) is the radial wave function and the upper limit of the integral is the muffin-tin radius \( R_s \).

It should be stressed here that the GG formula Eq. \cite{2} requires the use of an all electron potential and therefore it should not be compatible with pseudopotential methods.

Finally, \( T_c \) is evaluated using the Allen–Dynes equation \cite{32} as follows:

\[
T_c = f_1 f_2 \frac{\omega_{\log}}{1.2} \exp\left[-\frac{1.04(1+\lambda)}{\lambda-\mu^*(1+0.62\lambda)}\right] \tag{5}
\]

In Eq. \cite{5} \( \lambda = \lambda_X + 3\lambda_H \) where \( \lambda_X \) represent the acoustic modes of the element X and \( \lambda_H \) the optical modes of H. This separation is exact for these materials and was pointed out long time ago for other hydrides \cite{33}. We have set the Coulomb pseudopotential \( \mu^* = 0.1 \) and \( f_2 = 1 \). \( f_1 \) is the strong coupling factor given by the following

\[
f_1 = \left[1 + \left(\frac{\lambda}{2.46 + 9.35\mu^*}\right)^{1.5}\right]^{1/3}.
\]

The phonon dispersions and electron-phonon couplings are calculated using density functional perturbation theory (DFPT) \cite{34} and the plane-wave pseudopotential method implemented in Quantum-Espresso package \cite{35}, kinetic energy cutoff of 75 Ry and a \( 24 \times 24 \times 24 \) k-point and a \( 6 \times 6 \times 6 \) q-point mesh. The k-space integrations for DFPT were done with the tetrahedron method which corresponds to the zero-width condition in smearing.

A. Results and Analysis

Electronic structure

Fig. 1 shows the energy bands of H\textsubscript{3}Se in the \textit{Im\bar{3}m} crystal structure \cite{2} for three different lattice constants \( a=5.8 \) a.u., \( a=6.4 \) a.u. and \( a=7.2 \) a.u. that correspond to pressures \( P=2.45 \) Mbar, \( P=0.76 \) Mbar and \( P=0 \) respectively. Comparing Figs (a), (b) and (c) we note that for \( P=0 \) the lowest band is completely separated and forms a gap as is also shown in the DOS Fig. \cite{2} (c). This gap gradually closes for \( P=0.76 \) Mbar and \( P=2.45 \) Mbar. Our observation of the separated band at \( P=0 \) is stated for completeness and not as an explanation of the occurrence of superconductivity at higher pressure. The overall bandwidth increases significantly with increasing pressure as expected. However, for the high pressure cases near the Fermi level \( E_F \), the ordering and shape of the bands are not seriously affected. We note that these bands look very similar to those of the prototype material H\textsubscript{3}S. We have also calculated the energy bands of the other materials under investigation here i.e. for
X=As, Br, Sb, Te and I. The difference is basically in the position of \( E_F \), and therefore we will not present additional band structure figures but we will come back later to this point on the applicability of a rigid band behavior in these materials.

Similar information can also be found in Fig 2, which shows the total DOS (a)-(c), Se-site angular-momentum-decomposed DOS (d)-(f) and H-site DOS (g)-(i) of \( \text{H}_3\text{Se} \) where each column corresponds to \( P = 2.45 \) Mbar, \( P = 0.76 \) Mbar and \( P = 0 \) respectively. Consistent with Fig 1 at high pressures the shape of the DOS is preserved around \( E_F \), including the position of \( E_F \) on a sharp peak (van Hove singularity). In the equilibrium case (\( P=0 \)), the DOS at the Fermi level is composed of 50% of p-like Se and 20% of s-like H states suggesting a strong sp orbital hybridization. The d-like Se contribution to the DOS in Figs. 2(d)-(f), becomes larger as pressure increases. The percentage of d-like states is doubled from 6% in equilibrium condition to 13.5% at \( P = 2.45 \) Mbar. A similar pressure-enhanced trend, although much smaller in magnitude, also appears in the p-like H states as seen in Figs. 2(g)-(i).

Fig. 3 shows the \( \ell \)-components of the DOS at the Fermi level vs pressure for \( \text{H}_3\text{X} \) (X=As, Se and Br in the top row and Sb, Te and I in the bottom row). A tabulation of

\[
\begin{array}{ccccccccc}
\text{Pressure (Mbar)} & 0 & 1 & 2 & 3 & 4 & 5 & 6 & 7 & 8 \\
\text{\# of States} & 1 & 1 & 1 & 1 & 1 & 1 & 1 & 1 & 1 \\
\end{array}
\]

The percentage of d-like states is doubled from 50% of p-like Se to 100% at \( P = 2.45 \) Mbar. A similar pressure-enhanced trend, although much smaller in magnitude, also appears in the p-like H states as seen in Figs. 2(g)-(i).

![Energy bands of \( \text{H}_3\text{Se} \) under pressure](image1)

![Total DOS of \( \text{H}_3\text{X} \) vs pressure for X=As, Se, Br, Sb, Te and I](image2)

![Projected DOS of \( \text{H}_3\text{X} \) at Fermi level vs Pressure for X=As, Se, Br, Sb, Te and I](image3)
these results is found in Table I of the Appendix. All six materials show the p-like X component to be the dominant one with the $d_X$ and $s_H$ to have 2-3 times smaller values. However, the $d_X$ which is the smallest component in the equilibrium condition ($P = 0$), increases monotonically with the fastest rate in all cases. The important finding here is that the $p_H$ becomes significant at the high pressures where superconductivity occurs. We note that we present these results at low pressures to show the trends of the projected DOS within the $Im3m$ structure. However for these materials this structure is not stable at low pressures, as discussed in Ref. [37] the stable crystal structure is in the rhombohedral R3m space group [2].

*Hopfield parameter $\eta$*

We have calculated the Hopfield parameter $\eta_{j,l}$ using Eq. [2] in Section II. In this formulation the index $j$ indicates that we obtain separate $\eta$ for hydrogen and the element X. This also results in having two separate electron-phonon coupling constants $\lambda_j$ which give total $\lambda = \lambda_X + 3\lambda_H$. This approach differs from the approach of other authors, who directly compute the total $\lambda$. Our approach has the advantage of studying the electronic contribution to $\lambda$ from each element separately and being able to pin down which aspects of the band structure affect superconductivity as is described below. The summation Eq. [2] in a cubic approximation, has three terms which we identify as the sp (for $l=0$), pd (for $l=1$) and df (for $l=2$) channels. For the hydrogen component $\eta_H$ the dominant term comes from the sp channel. For the X component, $\eta_X$ of the H$_3$X compounds the dominant term comes from the pd channel. It should also be noted that each term of the sum consists of the product $\sin^2(\delta_l^j - \delta_{l+1}^j)\psi_{l+1}^j\psi_l^j$. The $\psi_{l+1}^j\psi_l^j$ term of the product is usually larger but the $\sin^2(\delta_l^j - \delta_{l+1}^j)$ is not negligible. In Fig. 4 $\eta_j$ is plotted versus pressure for the six materials we have studied. The values of $\eta_H$ have been multiplied by three because of the three crystallographic sites of hydrogen. From the six compounds, it is found that H$_3$Se has the largest values of $\eta$ but significantly smaller than those of the prototype material H$_3$S as shown in Fig. 4 (b). The others have lower values of $\eta$ especially those of the second row. We now proceed to analyze the relative importance of the two terms of the product shown in Fig. 5 and 6.

The term $\psi_{l+1}^j\psi_l^j$ in Eq. [2] plotted against pressure is shown in Fig. 5. One can see it retains the general trends and certain features such as few jumps and flatness at various pressure by comparing Fig. 5 to Fig. 3. Although the difference between X=Se and Te is more pronounced than others which can be attributed to the relative location of Fermi level to the peak in DOS, the rest are roughly in the same magnitude.

The second factor, $\sin^2(\delta_l^j - \delta_{l+1}^j)$, on the other hand, which describes the effect of phase shift as shown in Fig. 6 amplifies the difference and its influence can be summarized by the following trends. For H-site, while the $\sin^2(\delta_l^j - \delta_{l+1}^j)$ factor in the upper row is generally larger than that in the bottom row, $\sin^2(\delta_0^H - \delta_1^H)$ within the same row are nearly identical. For X elements the most significant contribution to $\sin^2(\delta_1^X - \delta_2^X)$ term cor-

![Figure 4](https://via.placeholder.com/150)

**FIG. 4:** Hopfield parameters $\eta$ vs pressure for H$_3$X. (a)-(f) correspond to X=As, Se, Br, Sb, Te and I respectively. $\eta_H$ has been multiplied by three. In (b) we also show $\eta$ for H$_3$S for comparison.

![Figure 5](https://via.placeholder.com/150)

**FIG. 5:** partial-DOS product terms in Eq. [2] vs. Pressure for H$_3$X at Fermi level. (a)-(f) each corresponds to X=As, Se, Br, Sb, Te and I respectively. Similar features as in Fig. 3 for the DOS are captured.
FIG. 6: Phase shift related factor \( \sin^2(\delta_{l-\delta_{l+1}}) \) vs. Pressure for \( H_2X \) at Fermi level. (a)-(f) each corresponds to \( X=\text{As, Se, Br, Sb, Te and I} \) respectively.

FIG. 7: (a)-(c) corresponds to \( N(E_F) \), \( \eta_j \) and \( \langle I_j^2 \rangle \) of \( H_3\text{Se} \) and (d)-(f) corresponds to those of \( H_3\text{Br} \) respectively.

As an example we plot the quantities \( N(E_F) \), \( \eta_X \) and \( \eta_{H} \) for \( X=\text{Br and Se} \) in Fig. [7]. we note that although \( \eta \)'s generally increase with increasing pressure, the underlying reasons are a bit different. In the case of \( H_3\text{Se}, \), \( N(E_F) \) is slowly varying with pressure while \( \eta \) and \( \langle I_j^2 \rangle \) have a rapid increase with pressure. In the case of \( H_3\text{Br}, \) the other hand, the \( N(E_F) \) decreases rapidly and competes with increasing \( \langle I_j^2 \rangle \). However, the important message is that the increase of \( \langle I_j^2 \rangle \) dominates over the \( N(E_F) \) with the resulting \( \eta \) to always increase with pressure.

Phonon frequencies and \( T_c \)

We retain the two-component approach separating the acoustic from the optic modes in these materials as justified by the small mass of hydrogen [33] and also verified by the lattice dynamics calculations of other groups [1] [5]. More importantly, we follow McMillan’s classic equation which separates the electron-phonon coupling constant \( \lambda_j \) into a numerator \( \eta_j \) which represents the electronic contribution and a force constant \( M_j \langle \omega^2_j \rangle \) in the denominator representing the phononic contribution. This separation is advantageous because it provides insights into understanding the reason superconductivity occurs in these materials.

The Hopfield-McMillan parameter \( \eta_j \) we analyzed in the previous section which we calculated directly by the Gaspari-Gyorffy theory, and identified the importance of the different terms in the GG formula. In order to calculate the force constants we recast McMillan Eq. [1] into the following form

\[
M_j \langle \omega^2_j \rangle = \frac{\eta_j}{\lambda_j}.
\] (6)

where \( \lambda_j \) is calculated from independent Quantum-Espresso for \( H_3\text{S}, H_3\text{As}, H_3\text{Se} \) and \( H_3\text{Br} \). The QE calculations, in addition, give \( \omega_{log} \) needed for \( T_c \). The results from both QE and the GG theory are summarized in Table 1. The results of \( H_3\text{As} \) from QE show negative phonon frequencies rendering this material as unstable.

Our QE results for both \( H_3\text{Se} \) and \( H_3\text{S} \) give values for \( \omega_{log} \) and \( \lambda \) very close to previous works Refs. [1] [5]. A small difference between our estimated \( T_c \) and Ref. [1] is partly due to a different value of \( \mu^* = 0.1 \) used in our calculations and because we also used a more general Allen-Dynes expression Eq. [5] including the mutliplier \( f_1 \), which is more suitable for large \( \lambda [25] \), rather than McMillan-Dynes expression [30] [38] implemented in QE by default.

In Table 1 we show \( N(E_F) \) calculated by the LAPW method, \( \eta_j \) by the GG theory, \( \lambda_j, \omega_{log} \) and \( \omega_j \) by the QE code.

This Table 1 shows that hydrogen is the main contributor to the \( T_c \) in all three calculated materials as it makes up more than 75% of the total \( \lambda \) while providing higher frequency vibrational modes.
TABLE I: \(N(E_F)\) and \(\eta\) calculated using LAPW and GG theory for \(H_3X\) (X=As, Se, Br, Sb, Te and I) and \(\lambda_j\), \(\omega_{log}\) and \(\sqrt{\langle \omega_j^2 \rangle}\) calculated using QE for X=S, Se and Br.

<table>
<thead>
<tr>
<th>(N(E_F)) states (\text{#} )</th>
<th>(\eta_X)</th>
<th>(\eta_H)</th>
<th>(M_X\langle \omega_X^2 \rangle) (eV/Å(^2))</th>
<th>(M_H\langle \omega_H^2 \rangle) (eV/Å(^2))</th>
<th>(\omega_{log}) (\sqrt{\langle \omega_X^2 \rangle}) (K)</th>
<th>(\sqrt{\langle \omega_H^2 \rangle}) (K)</th>
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<th>(T_c) (K)</th>
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<tr>
<td>(H_3S)</td>
<td>8.78</td>
<td>7.68</td>
<td>2.29</td>
<td>17.08</td>
<td>4.11</td>
<td>1348</td>
<td>546</td>
<td>1514</td>
<td>0.46</td>
<td>1.68</td>
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<td>(H_3As)</td>
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<td>(H_3Se)</td>
<td>6.70</td>
<td>3.90</td>
<td>1.68</td>
<td>17.62</td>
<td>5.60</td>
<td>1357</td>
<td>353</td>
<td>1762</td>
<td>0.22</td>
<td>0.91</td>
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<tr>
<td>(H_3Br)</td>
<td>5.85</td>
<td>4.19</td>
<td>1.33</td>
<td>13.84</td>
<td>4.22</td>
<td>986</td>
<td>311</td>
<td>1536</td>
<td>0.30</td>
<td>0.96</td>
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<td>(H_3Sb)</td>
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The optical phonon frequency \(\langle \omega_X^2 \rangle^{1/2}\) is generally insensitive to the X element that hydrogen forms hydrides with as long as the \(M_X\) is large enough to ensure the phonon mode separation. The difference in \(\langle \omega_X^2 \rangle^{1/2}\) between \(H_3Se\) and \(H_3S\) is less than 10%. The lower frequency acoustic branch \(\langle \omega_X^2 \rangle^{1/2}\) on the other hand, varies more significantly, as X represents a different element in a different hydride, depending on the bonding and the atomic mass of the X element. As expected \(\omega_{log}\) could also have noticeable change as it accounts for the collective behavior of all elements in the material. However the influence of the phonon frequencies on \(T_c\) is more limited due to the fact that \(\omega_{log}\) and \(\langle \omega_j^2 \rangle^{1/2}\) enter different parts of Eq. 5 and have opposite effect on \(T_c\) as they are correlated.

For instance, while having slightly smaller \(\eta\)'s in \(H_3Br\) \((\eta_{Se} = 4.19\) and \(\eta_{H} = 1.33\) eV/Å\(^2\)) than \(H_3Se\), the \(\lambda\) of \(H_3Br\) is about 10% larger than that of \(H_3Se\) at the \(P = 2\) Mbar. This is mainly because \(H_3Br\) has smaller \(\omega_j\)'s in the denominator of Eq. 1. The decrease of \(\omega_j\) in \(H_3Br\) which leads to the increase of \(\lambda\), will also reflect on the prefactor \(\omega_{log}\) in Eq. 5 which lowers the \(T_c\). As a result, with similar \(\eta\) values in both \(H_3Se\) and \(H_3Br\), having nearly 32% larger \(\omega_{log}\) in \(H_3Se\) only gives 18% difference in its \(T_c\).

The importance of \(\omega_{log}\) in high \(T_c\) superconductivity is sometimes overemphasized. \(H_3Se\) and \(H_3S\) have very similar \(\omega_{log}\), however the \(T_c\) of \(H_3S\) is higher by more than 100 K. On the other hand, as discussed earlier, \(H_3Se\) and \(H_3Br\) having similar \(\eta\) values leads to vary close \(T_c\) despite the significant \(\omega_{log}\) difference.

The reason becomes clear by comparing the \(\eta\) of \(H_3X\) (X=Se, Br and S) in Fig. 2. It is obvious that only \(H_3S\) has distinctively large \(\eta\) and therefore allows the system to have both large \(\omega_{log}\) and \(\lambda\).

Although from a numerical standpoint, a high \(T_c\) is rather the optimal condition of the interplay between \(\lambda_j\) and \(\omega_{log}\) as in the case of \(H_3S\). The parameter \(\eta\) which depends solely on the electronic structure, is the only factor that can be optimized independently.

The value of the Hopfield parameters \(\eta_j\) can in principal change by a lot more because they depend on the Fermi level values of the angular momentum decomposed electronic densities of states and how close to a van Hove singularity the Fermi level is. So our finding is that the Hopfield parameter is a quantity more sensitive from material to material than the average phonon frequency. Therefore, our conclusion is that within the \(Im\ 3m\) crystal structure a significant increase of the Hopfield parameter from its value in \(H_3S\) is needed in order to raise \(T_c\) in the direction of room temperature. We believe that values of \(\eta_j\) larger than 10 eV/Å\(^2\) are needed for higher \(T_c\) than in \(H_3S\).

Our approach based on the GG theory has the advantage of keeping the decoupling of the electronic component of \(\lambda\) from the phonon component. In addition, separating the contribution of the element X from that of hydrogen identifies the distinct contributions of acoustic and optic modes. So those two decouplings i.e. separation of electronic from phononic contributions and separation of the two elements X and H offer more insights in the understanding of superconductivity in these materials.

Regarding the three materials in the second row we found small values of \(\eta\) and we conclude that given their larger masses it is unlikely that their force constants would be small enough to raise \(\lambda\) to the desired value for high \(T_c\). Therefore we did not carry out phonon spectra calculations for those.

**Rigid-band model**

Fig. 8 shows the total DOS near \(E_F\) and partial DOS for all three materials in the first row (X=As, Se and Br) at Pressure around 2 Mbar. By comparing the three panels, one can see that the shape of DOS around \(E_F\) is well preserved. The relevant electronic properties can thus be explained with a rigid-band model where the change in electronic states corresponds directly to Fermi level shift due to a small amount of alloying and indirectly affect \(T_c\) through the parameter \(\eta_j\).

To better understand how the electronic properties
could potentially affect $\lambda$ and $T_c$, we also consider $T_c$ versus electron number within a rigid band model. This is shown in Fig. 9. Each material has its Fermi level near a peak in the density of states, even without alloying. By shifting the Fermi level toward the peak, the $\lambda$ and $T_c$ can be enhanced dramatically as in the case of $H_3Br$. However for $H_3Se$ the enhancement is limited since $E_F$ is very close to the van Hove singularity.

This gives an interpretation on the role of the element X from a different perspective and provides certain guidelines for optimizing hydrides to achieving high $T_c$. Of special interest is the case of $H_3Br$, where a small amount of additional electrons can enhance the $T_c$ to above 150 K. This may be accomplished by increasing the hydrogen content in $H_3Br$. We confirmed this rigid band prediction by performing a virtual crystal calculation by increasing the hydrogen amount by 0.15 electrons.

It should be mentioned here that the idea of substitution of the element X has been applied in the H-S-Se system by Liu et al. [39] who discovered three dynamically stable structures which keep the main features of the cubic Im$\overline{3}m$ structure. Along the same lines, Amsler [40] using cluster expansion method reached the same conclusions and that $T_c$ cannot be raised beyond its value in $H_3S$ because of the Fermi level moving away from the van Hove singularity.

FIG. 8: DOS for $H_3X$ (X=As, Se and Br). The DOS within ± 0.3 (Ry) around $E_F$ is preserved well across adjacent X elements belonging to the same period.

FIG. 9: Estimated $T_c$ in the case of alloying using rigid band model for (a) $H_3Se$ and (b) $H_3Br$.

III. CONCLUSIONS

We have calculated the parameters determining superconductivity in the group of hydrides $H_3X$ (X=As, Se, Sb, Te and I). Our approach combines LAPW electronic-structure calculations, which yield the total and angular momentum decomposed DOS in the Im$\overline{3}m$ crystal structure, with the Quantum-ESPRESSO code from which the phonon spectra are calculated.

We also use the Gaspari–Gyorffy theory to evaluate the McMillan-Hopfield parameter $\eta$ and obtain additional insight on the mechanism of superconductivity in these materials. We conclude that the elements X play the role of stabilizer of these compounds to keep H metallized under pressure. The highest superconducting transition temperature 112 K is found for $H_3Se$, which is isoelectronic to the well-established $H_3S$.

For $H_3Br$ we calculate a little smaller $T_c = 98$ K, but using a rigid band model and a VCA calculation we predict $T_c \sim 150$ K with electron doping.

We find that the road to high $T_c$ depends mainly on high values of the Hopfield parameters on the hydrogen sites. Our analysis shows that the variation of the parameters $\eta_H$ or of the matrix element $\langle I^2 \rangle$ is more important than the variation of the phonon frequency.

This is consistent with the view of Pickett and Eremets [41] who argue that “obtaining and understanding, and thereby control, of $\langle I^2 \rangle$ is one of the most important remaining questions in researcher’s quest to further increase $T_c$ or to reduce the necessary pressure”.

Finally, in Refs. [4, 6] the possibility of achieving higher $T_c$ in $H_3S$ by adding small amount of phosphorus is explored with conflicting results. Also, Heil and Boeri [12] suggest raising $T_c$ in $H_3S$ by replacing sulfur with oxygen. In our present study we did not find ways to raise $\langle I^2 \rangle$ or $\eta$ resulting in a higher $T_c$ in the group of compounds $H_3X$ that we used. Ref. [9] reports a very large $\eta_F = 17.5$ eV/Å$^2$ for $H_3F$, but the stability of this material is in question. In a preliminary calculation for $H_3O$ we have found a very large value of $\eta_0 = 18.4$ eV/Å$^2$ without exploring the stability of the Im$\overline{3}m$ structure.

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Appendix A

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[33] B. M. Klein and D. A. Papaconstantopoulos. On cal-
TABLE II: Total and projected DOS, Hopfield parameter $\eta$ and the two terms of the products in Eq. 2.


